



1NM70-Q

Preliminary

Power MOSFET

**1A, 700V N-CHANNEL
SUPER-JUNCTION MOSFET**

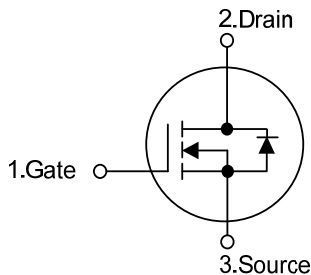
■ DESCRIPTION

The **UTC 1NM70-Q** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} < 5.4\Omega @ V_{GS} = 10V, I_D = 0.5A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

■ SYMBOL

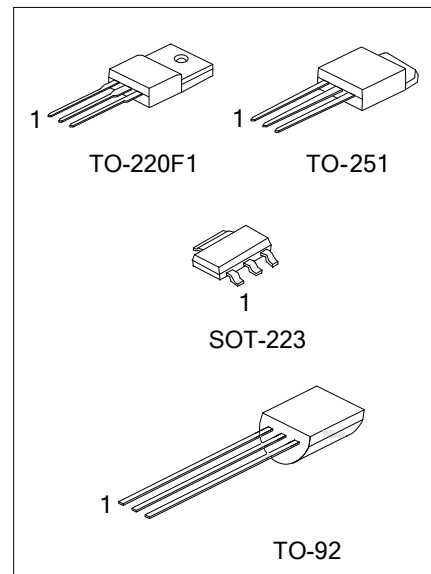


■ ORDERING INFORMATION

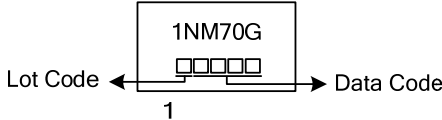
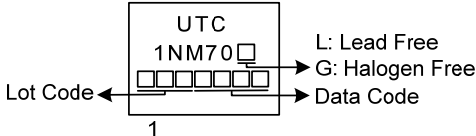
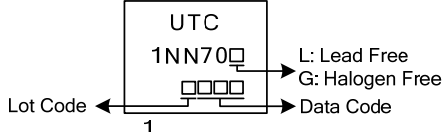
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	1NM70G-AA3-R	SOT-223	G	D	S	Tape Reel
1NM70L-TF1-R	1NM70G-TF1-R	TO-220F1	G	D	S	Tape Reel
1NM70L-TM3-R	1NM70G-TM3-R	TO-251	G	D	S	Tape Reel
1NM70L-T92-B	1NM70G-T92-B	TO-92	G	D	S	Tape Box
1NM70L-T92-K	1NM70G-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1NM70G-AA3-R</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AA3: SOT-223, TF1: TO-220F1, TM3: TO-251, T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING

Package	Marking
SOT-223	 <p>1NM70G</p> <p>Lot Code ← [] → Data Code</p> <p>1</p>
TO-220F1 / TO-251	 <p>UTC</p> <p>1NM70</p> <p>Lot Code ← [] → Data Code</p> <p>L: Lead Free</p> <p>G: Halogen Free</p> <p>1</p>
TO-92	 <p>UTC</p> <p>1NN70</p> <p>Lot Code ← [] → Data Code</p> <p>L: Lead Free</p> <p>G: Halogen Free</p> <p>1</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	1.0	A
	Pulsed (Note 2)	I_{DM}	4.0	A
Avalanche Current (Note 2)		I_{AR}	0.7	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	34	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.5	V/ns
Power Dissipation	SOT-223	P_D	8	W
	TO-220F1		21	W
	TO-251		28	W
	TO-92		1.6	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=138\text{mH}$, $I_{AS}=0.7\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 1.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-220F1		62.5	$^\circ\text{C}/\text{W}$
	TO-251		110	$^\circ\text{C}/\text{W}$
	TO-92		180	$^\circ\text{C}/\text{W}$
Junction to Case	SOT-223	θ_{JC}	15.6	$^\circ\text{C}/\text{W}$
	TO-220F1		5.95	$^\circ\text{C}/\text{W}$
	TO-251		4.46	$^\circ\text{C}/\text{W}$
	TO-92		78	$^\circ\text{C}/\text{W}$

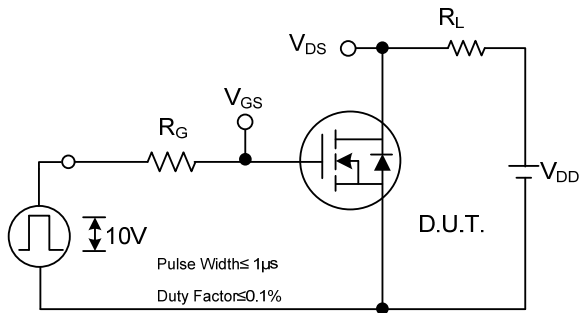
■ ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			10	μA
Gate-Source Leakage Current	Forward	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.5A$			5.4	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		83		pF
Output Capacitance	C_{OSS}			37		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50V, V_{GS}=10V, I_D=0.5A$ $I_G=100\mu A$ (Note 1, 2)		12.3		nC
Gate-Source Charge	Q_{GS}			2		nC
Gate-Drain Charge	Q_{GD}			4		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30V, V_{GS}=10V, I_D=0.5A,$ $R_G=25\Omega$ (Note 1, 2)		35		ns
Turn-On Rise Time	t_R			21		ns
Turn-Off Delay Time	$t_{D(OFF)}$			53		ns
Turn-Off Fall Time	t_F			18		ns
DRAIN-SOURCE DIODE CHARACTERISTICS						
Continuous Drain-Source Current	I_S				1.0	A
Maximum Body-Diode Pulsed Current	I_{SM}				4.0	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=1.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=1.0A, V_{GS}=0V,$ $di_f/dt=100A/\mu s$		200		nS
Body Diode Reverse Recovery Charge	Q_{rr}				0.63	

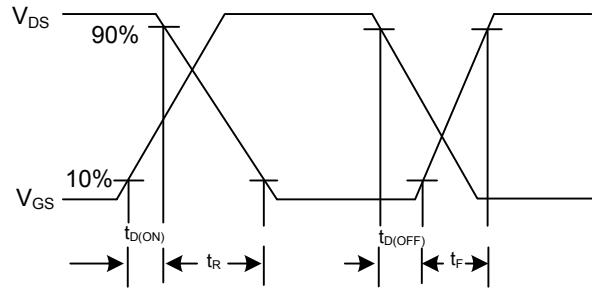
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

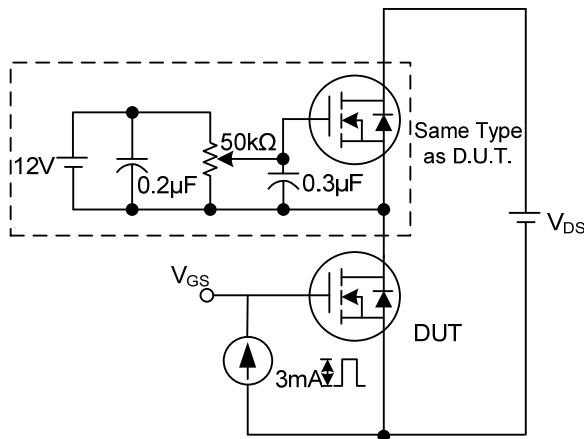
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



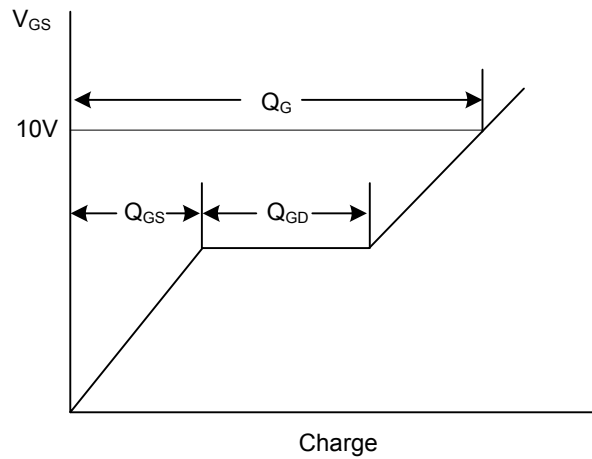
Switching Test Circuit



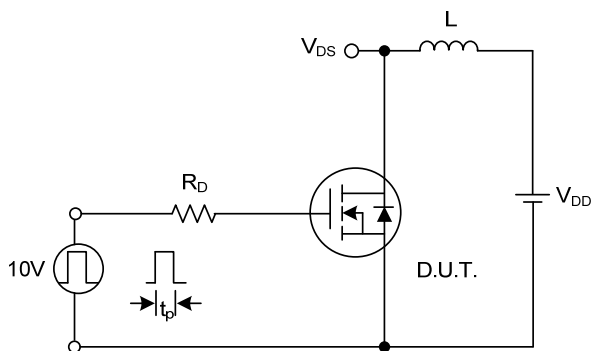
Switching Waveforms



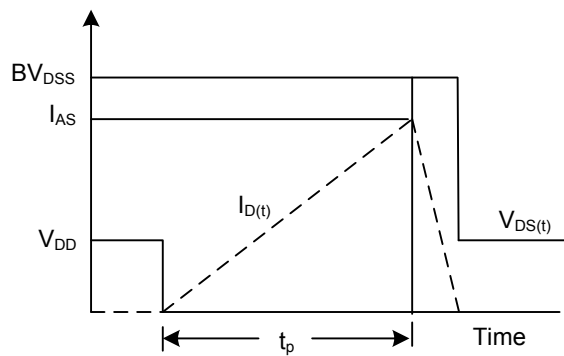
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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